

## Avionics Band RF Power LDMOS FET

The high power transistor part number ILD1011M150 is designed for Avionics systems operating at 1030-1090 MHz. Operating at 50µs, 2% pulse conditions this LDMOS FET device supplies a minimum of 150 watts of power at 1030/1090 MHz. All devices are 100% screened for large signal RF parameters.



### Silicon LDMOS FET

- High Power Gain
- Superior thermal stability

### Class AB Operation

- Gate biased to  $I_{DQ} = 10 \text{ mA}$

### Configuration

- Common Source

### Gold Metal

- Maximum Reliability

### Package

- Thermally enhanced
- Pb-free and RoHS-compliant

### Epoxy Sealed Lid

- Gross Leak Qualified

### RF Test Fixture

- Broadband
- Matched to 50 ohms
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning required

## TYPICAL DATA      TYPICAL DATA      TYPICAL DATA      TYPICAL DATA

Devices	Freq	V <sub>DD</sub>	P <sub>IN</sub>	IRL	P <sub>OUT</sub>	Gain	I <sub>PK</sub>	n <sub>d</sub>	n' <sub>d</sub>	Droop	VSWR	
	(MHz)	(V)	(W)	(dB)	(W)	(dB)	(A)	(%)	(%)	(dB)	1.5:1	20:1
D4514-2	1090	32	7	11	163	13.67	9.7	52.5	55.4	0	S	P
D4514-5	1090	32	7	17	164	13.70	10.1	50.7	53.4	0	S	P

Pulse format = 50µs, 2%, I<sub>DQ</sub> = 10Ma

n<sub>d</sub>= Drain efficiency (including bias current)

n'<sub>d</sub>= Drain efficiency (excluding bias current)

**MAXIMUM RATINGS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Drain-Source Voltage	$V_{DS}$	--	70	V	--
BD	Gate-Source Voltage	$V_{GS}$	-0.5	12	V	--
BD	Storage Temperature Range	$T_{STG}$	-55	+200	°C	--
BD	Operating Junction Temperature Range	$T_J$	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

**THERMAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	0.056	°C/W	$V_D=32V, I_{DQ}=10mA, T_F=25\pm 5^\circ C, P_{OUT}=150W$
Note	Screen 'BD' = parameter qualified By Design.					

**PROCESSING SPECIFICATIONS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification.
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification.
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

**DC ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Drain-Source Breakdown Voltage	$BV_{DSS}$	70	--	V	$I_D = 10mA, V_{GS} = 0V, T_F = 25\pm 5^\circ C$
100%	Drain Leakage Current	$I_{DSS}$	--	100	$\mu A$	$V_{DS} = 28V, V_{GS} = 0V, T_F = 25\pm 5^\circ C$
100%	Gate Threshold Voltage	$V_{GSTH2}$	2.5	5.0	V	$I_D = 100mA, T_F = 25\pm 5^\circ C, V_{DS} = 5V$
100%	Gate Leakage Current	$I_{GSS}$	-	1	$\mu A$	$V_{GS} = 5V, V_{DS} = 0V, T_F = 25\pm 5^\circ C$

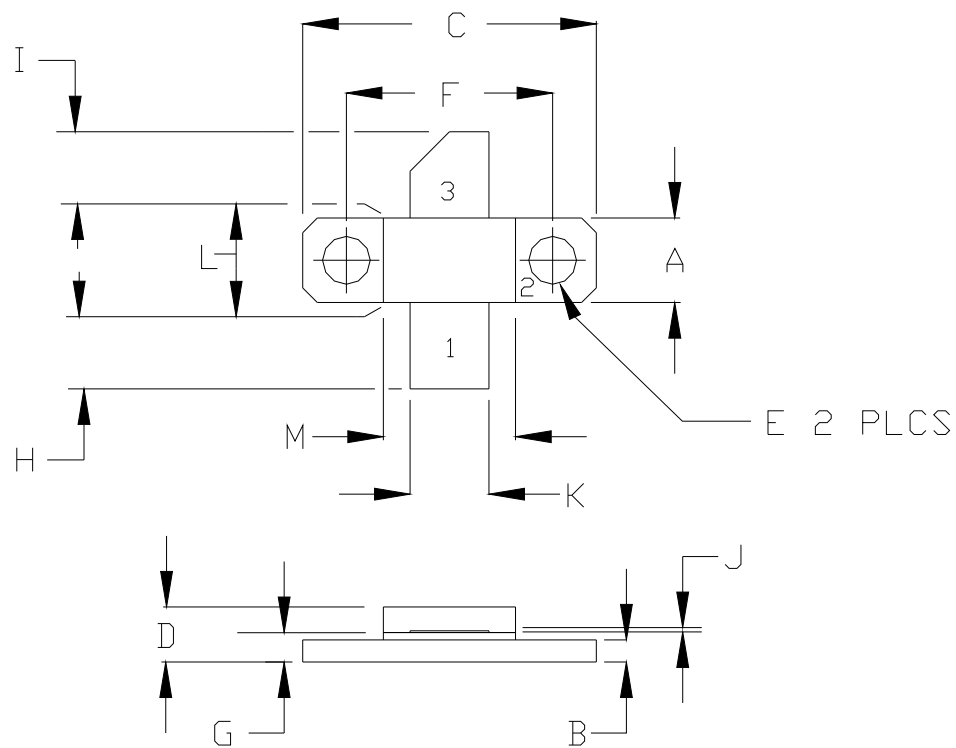
**RF ELECTRICAL CHARACTERISTICS**

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	18	-10	dB	$V_{DD}=32V, P_{IN}=7W, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$
BD	Maximum Overdrive	$P_{IN(MAX)}$		12	W	$V_{DD}=32V, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$
100%	Power Gain	$G_P$	13.3	14.8	dB	$V_{DD}=32V, P_{IN}=7W, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$
100%	Drain Efficiency ( $P_O/I_D/V_{DD}$ )	$N_d$	50	80	%	$V_{DD}=32V, P_{IN}=7W, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$
100%	Pulse Amplitude Droop	D	-0.5	0.5	dB	$V_{DD}=32V, P_{IN}=7W, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$
100%	Stability into 1.5:1 VSWR	VSWR-S			--	$V_{DD}=32V, P_{IN}=7W, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$ Rotate 1.5:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
BD	Load Mismatch Tolerance	LMT		20:1	--	$V_{DD}=32V, P_{IN}=7W, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$ Rotate 20:1 output VSWR through 360° phase. Survival.
BD	Pulse Risetime	RT		60	ns	$V_{DD}=32V, P_{IN}=7W, \text{Pulse}=50\mu s, 2\%, T_F=25\pm 5^\circ C, F=F1, I_{DQ}=10mA.$ Measure between 10% and 90% detected power points.
Note 1	F1 = 1030/1090 MHz.					
Note 2	Pulse format = 50µs, 2%					
Note 3	$T_F$ = Device flange temperature.					
Note 4	Screen 'BD' = parameter qualified By Design.					

**RF TEST FIXTURE IMPEDANCE CHARACTERISTICS**

Frequency (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
1030 (Optimal)	1.42-j0.20	1.43-j1.00
1090 (Actual + Optimal)	0.63-j0.50	1.34-j0.97
Impedance Definition		

**PACKAGE DIMENSIONAL OUTLINE DRAWING**



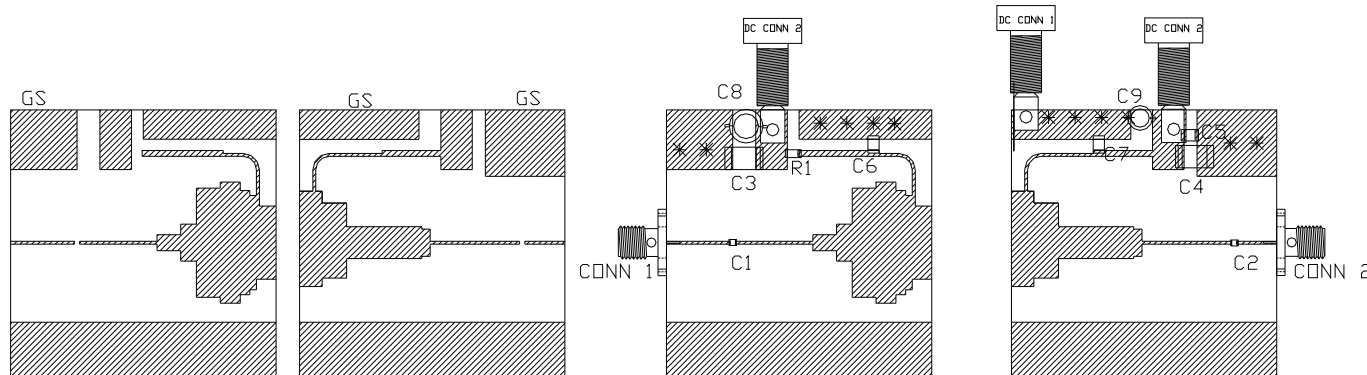
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.225	0.235	5.71	5.96
B	0.055	0.065	1.40	1.65
C	0.795	0.805	20.19	20.44
D	0.140	0.160	3.55	4.06
E	0.125	0.135	3.18	3.43
F	0.557	0.567	14.14	14.40
G	0.077	0.087	1.95	2.20
H	0.215	0.245	5.46	6.22
I	0.215	0.245	5.46	6.22
J	0.004	0.006	0.10	0.15
K	0.210	0.220	5.33	5.58
L	0.225	0.235	5.71	5.96
M	0.355	0.365	9.01	9.27

PIN SCHEDULE	
1	GATE
2	SOURCE
3	DRAIN

NOTES:  
LID: LID-PL32-1

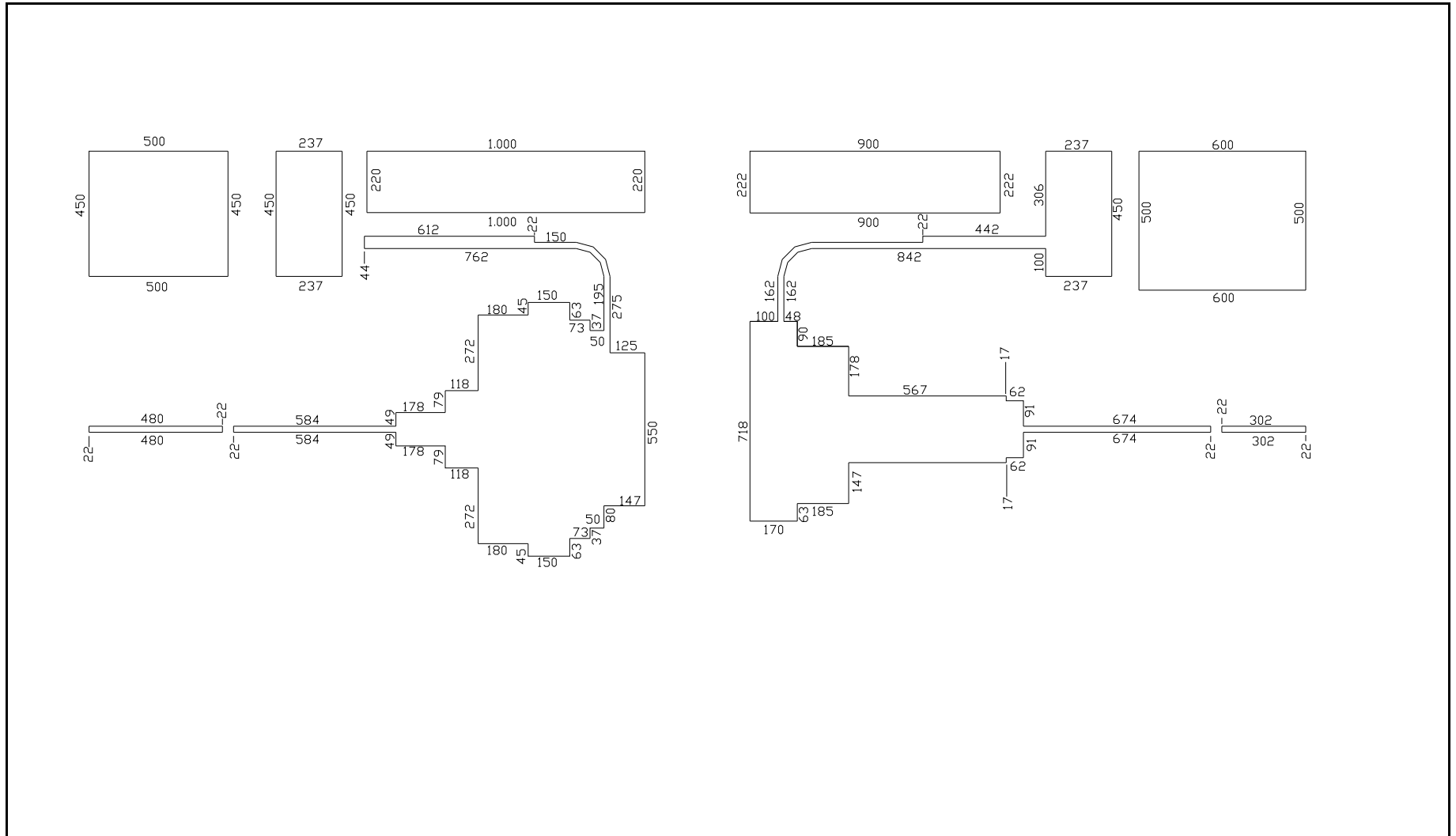
**RF TEST FIXTURE – ASSEMBLY AND PARTS LIST**

**1090 MHZ CIRCUIT**

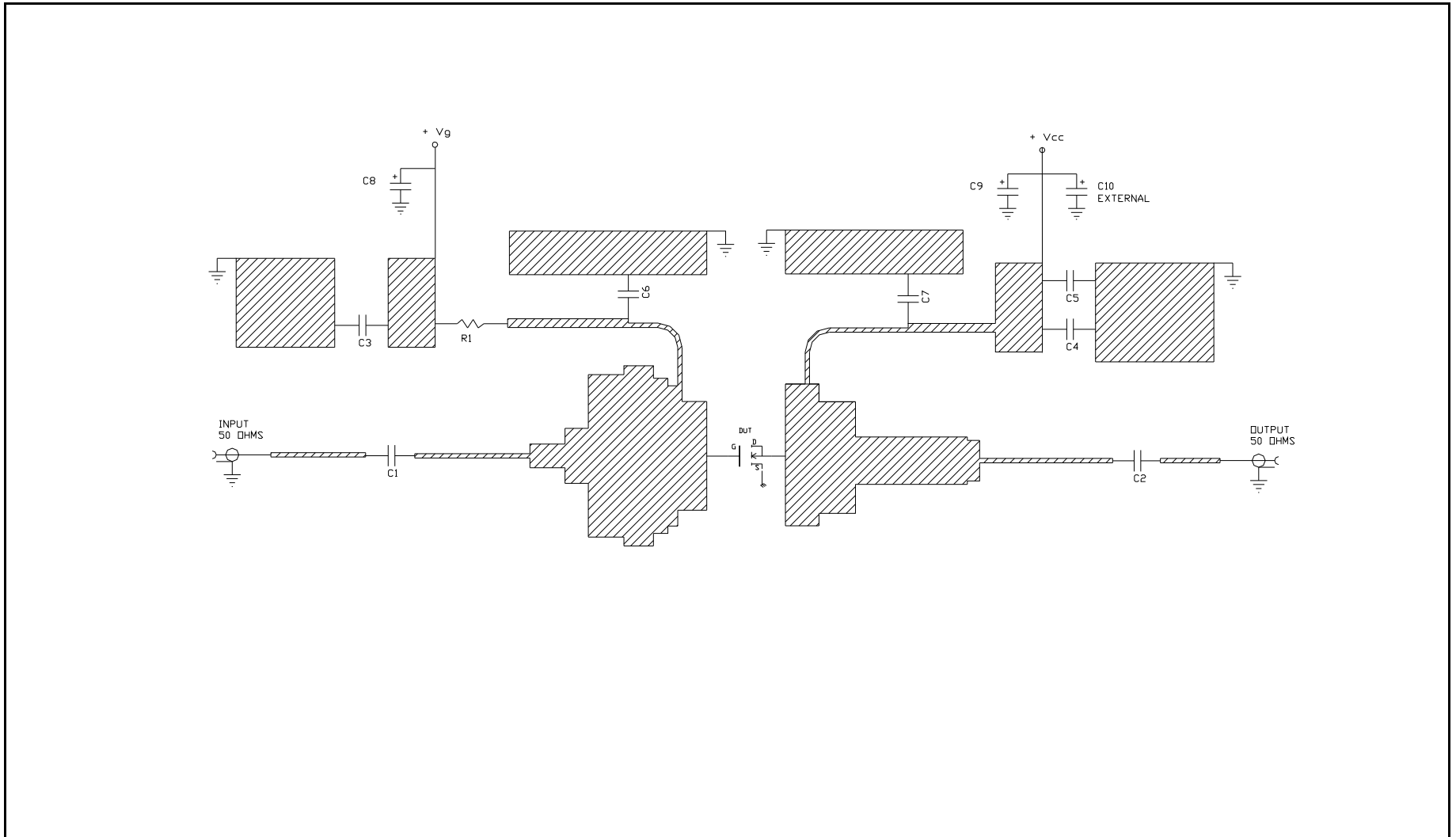


COMPONENT	DESCRIPTION
DUT	TRANSISTOR #ILD1011M150, MOUNT HARD TO THE RIGHT
PC BOARD	ROGERS #RD 3010 10.2" 1oz. Cu
C1, C2	CHIP CAPACITOR ATC100A-39 pF
C3, C4	TANTALUM - AVX 4.7uF 50V ESR = 0.3ohms
C5	CERAMIC CHIP CAPACITOR ATC100B - 1000 pF 250V
C6, C7	CERAMIC CHIP CAPACITOR ATC100B - 47 pF
C8, C9	ELECTROLYTIC CAPACITOR 68uF / 63V
C10 (NOT SHOWN)	STORAGE CAPACITOR CORNELL DUBILIER ALUMINUM FLAT PACK "MLP" SERIES OR SIMILAR FOR STORAGE CAPACITOR
R1	RESISTOR 120ohms - 300 ohms
GS (12 PLACES)	GROUND SHIM, COPPER, TH=0.001"
CONN 1, CONN 2	SMA CONNECTOR, DS #2052-5636-02
INPUT PC BOARD CARRIER	2 INCH BRASS-07 (2.0")
OUTPUT PC BOARD CARRIER	2 INCH BRASS-07 (2.0")
TRANSISTOR CARRIER	2 INCH COPPER- 11
TRANSISTOR CLAMP	NDRLY CLAMP-01 (Pl 32)
ALUMINUM HEATSINK	2 INCH HEAT SINK-11
DC CONN 1	BANANA JACK, BLACK 1 PLACE (GROUND)
DC CONN 2	BANANA JACK, RED 2 PLACES
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST

**RF TEST FIXTURE – CIRCUIT DIMENSIONS IN MILS**



**RF TEST FIXTURE – ELECTRICAL SCHEMATIC**



**DEFINITIONS**

<b>Data Sheet Status</b>	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
<b>Maximum Ratings</b>	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only. Operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

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